TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

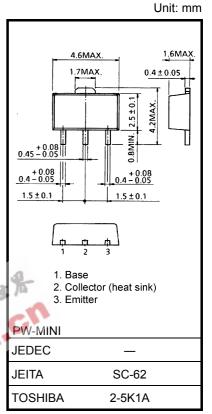
2SA1735

Power Amplifier Applications Power Switching Applications

- Low saturation voltage: $V_{CE (sat)} = -0.5 \text{ V (max) (IC} = -500 \text{ mA)}$
- High speed switching time: $t_{stg} = 0.25 \,\mu s$ (typ.)
- Small flat package
- PC = 1.0 to 2.0 W (mounted on a ceramic substrate)
- Complementary to 2SC4540

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	-60	V	
Collector-emitter voltage	V _{CEO}	-50	V	
Emitter-base voltage	V _{EBO}	-6	V	
Collector current	IC	-1	A	
Base current	ΙΒ	-0.2	Α	
	PC	500	mW	
Collector power dissipation	PC	1000		
	(Note 1)	1000		
Junction temperature	Тј	150	°C	
Storage temperature range	T _{stg}	−55 to 150	°C	



Weight: 0.05 g (typ.)

Note 1: Mounted on a ceramic substrate (250 mm² × 0.8 t)

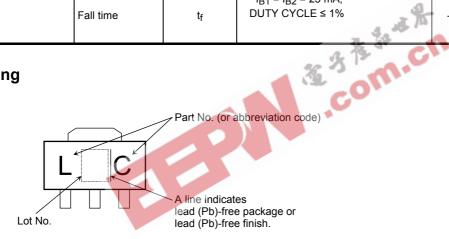
Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

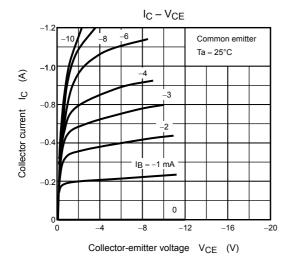
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

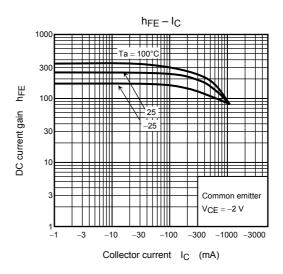
Electrical Characteristics (Ta = 25°C)

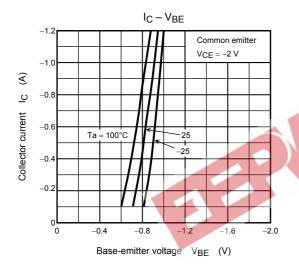
Charac	eteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off cu	rrent	I _{CBO}	V _{CB} = -60 V, I _E = 0	_	_	-0.1	μΑ
Emitter cut-off current		I _{EBO}	V _{EB} = -6 V, I _C = 0	_	_	-0.1	μΑ
Collector-emitter breakdown voltage V (I		V (BR) CEO	I _C = -10 mA, I _B = 0	-50	_	_	V
DC current gain		h _{FE (1)}	V _{CE} = -2 V, I _C = -100 mA	120	_	400	
		h _{FE} (2)	V _{CE} = -2 V, I _C = -700 mA	40	_	_	
Collector-emitter sa	aturation voltage	V _{CE} (sat)	I _C = -500 mA, I _B = -25 mA	_	_	-0.5	V
Base-emitter saturation voltage		V _{BE} (sat)	I _C = -500 mA, I _B = -25 mA	_	_	-1.2	V
Transition frequency		f _T	V _{CE} = -2 V, I _C = -100 mA	_	100	_	MHz
Collector output capacitance		C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	_	16	_	pF
Switching time	Turn-on time	t _{on}	$\begin{array}{c c} I_{B2} & \text{OUTPUT} \\ \hline I_{B1} & \overline{)} & \overline{)} & \overline{)} \\ \hline I_{B1} & \overline{)} & \overline{)} & \overline{)} \\ \hline 20 \ \mu s & \overline{)} & \overline{)} \\ \hline -I_{B1} = I_{B2} = 25 \ \text{mA,} \\ \hline DUTY CYCLE \le 1\% \end{array}$	_	0.1	_	
	Storage time	t _{stg}		_	0.25	_	μs
	Fall time	t _f		_	0.1	_	

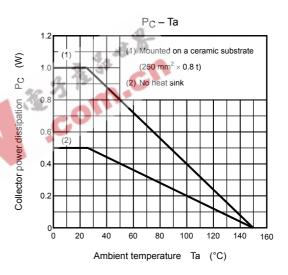
Marking











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